



Digital laser printing and sintering of silver nanoparticle inks for the additive manufacturing of micro-conductive patterns on non-planar flexible substrates

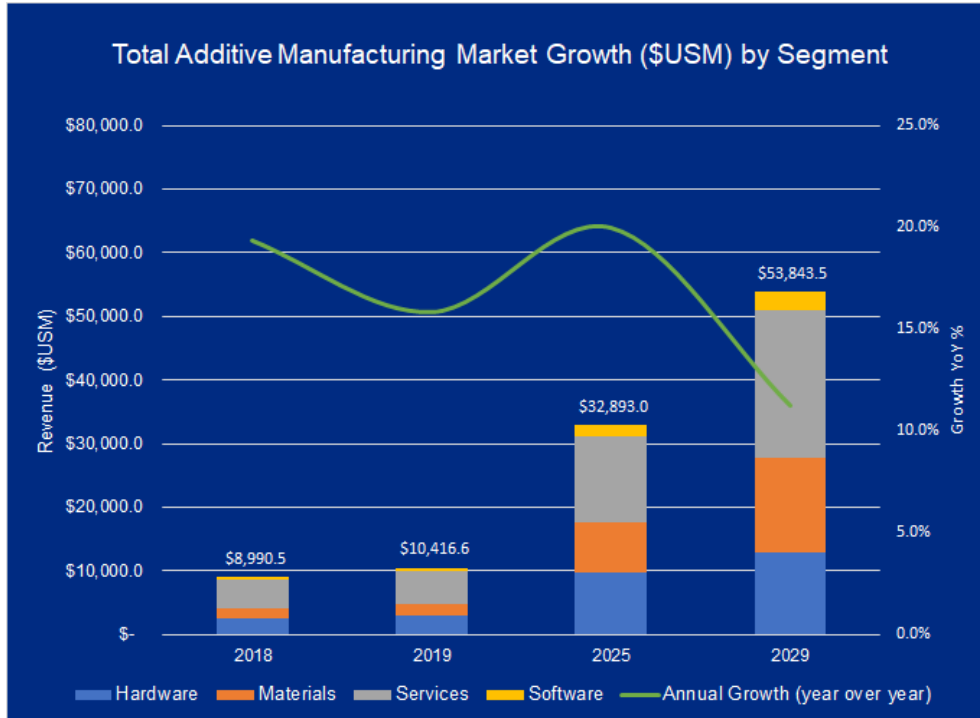
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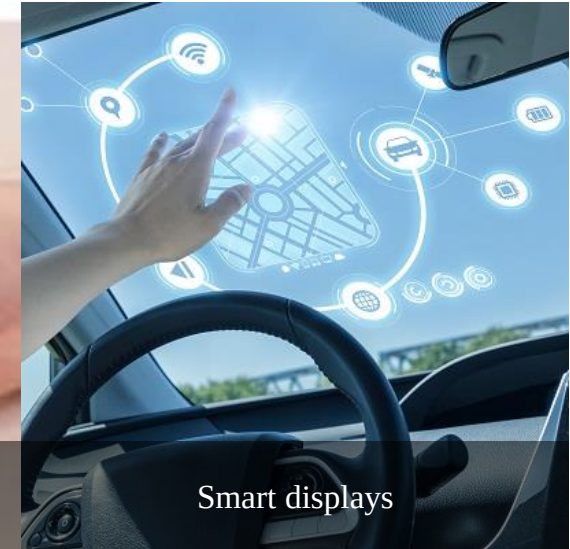
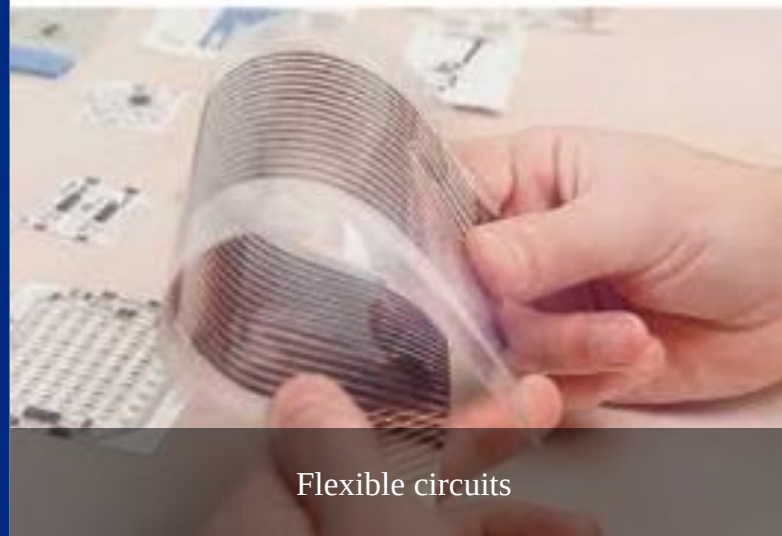
²PV Nano Cell Ltd, Israel

³FlexEnable Ltd, United Kingdom

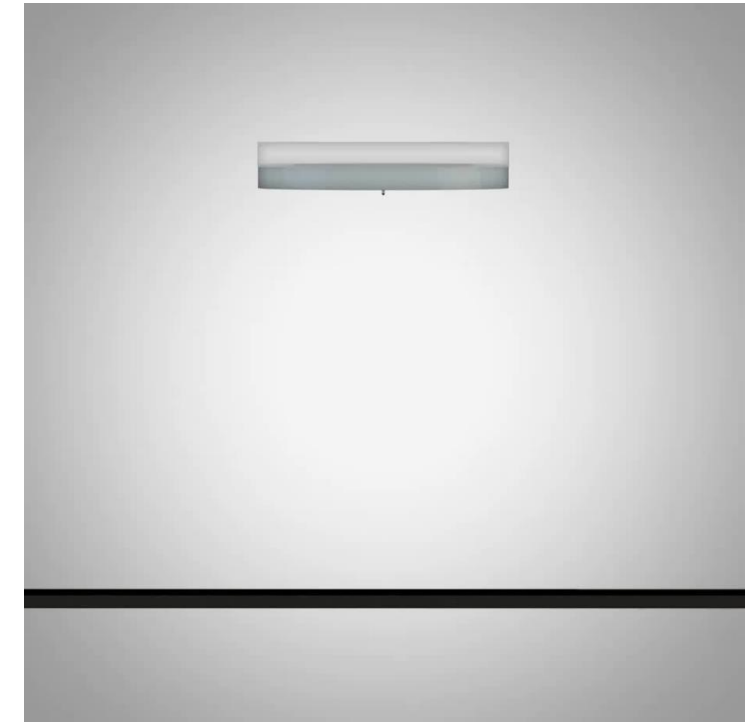
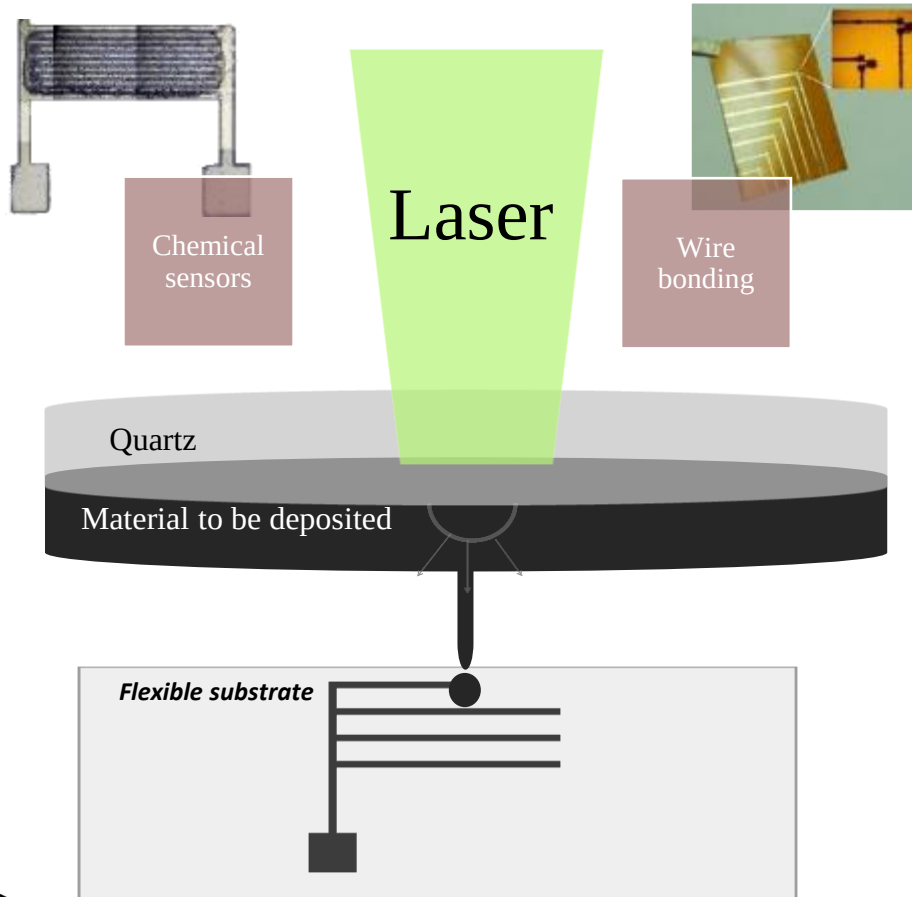
Additive manufacturing



SmarTech Markets Publishing



Laser induced forward transfer (LIFT)

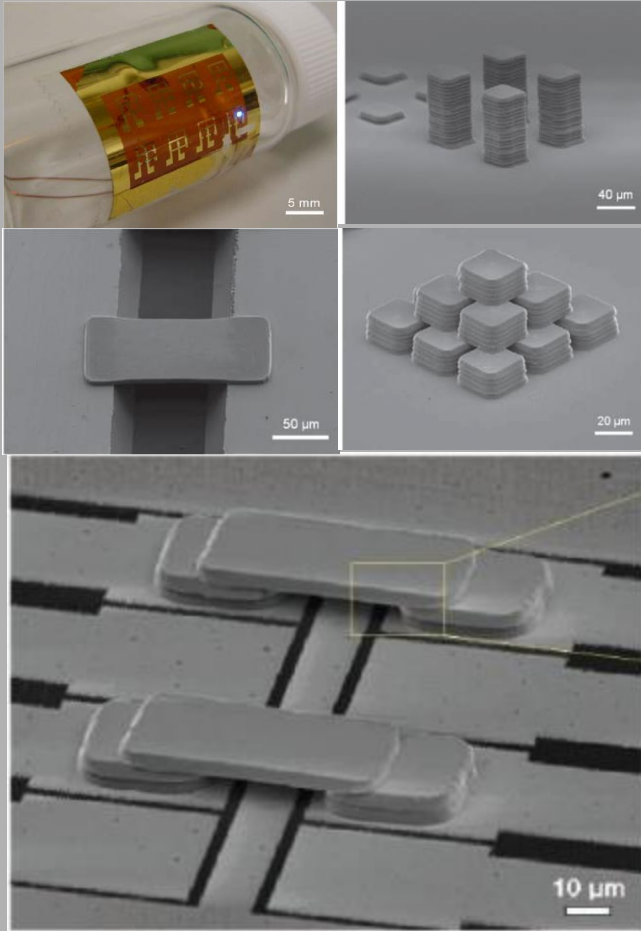


- Printing in solid, liquid phase and 2D materials
- Spatial resolution down to 10 μm for liquid and sub-micron for solid phase
- Printing of inorganic, organic, biological materials

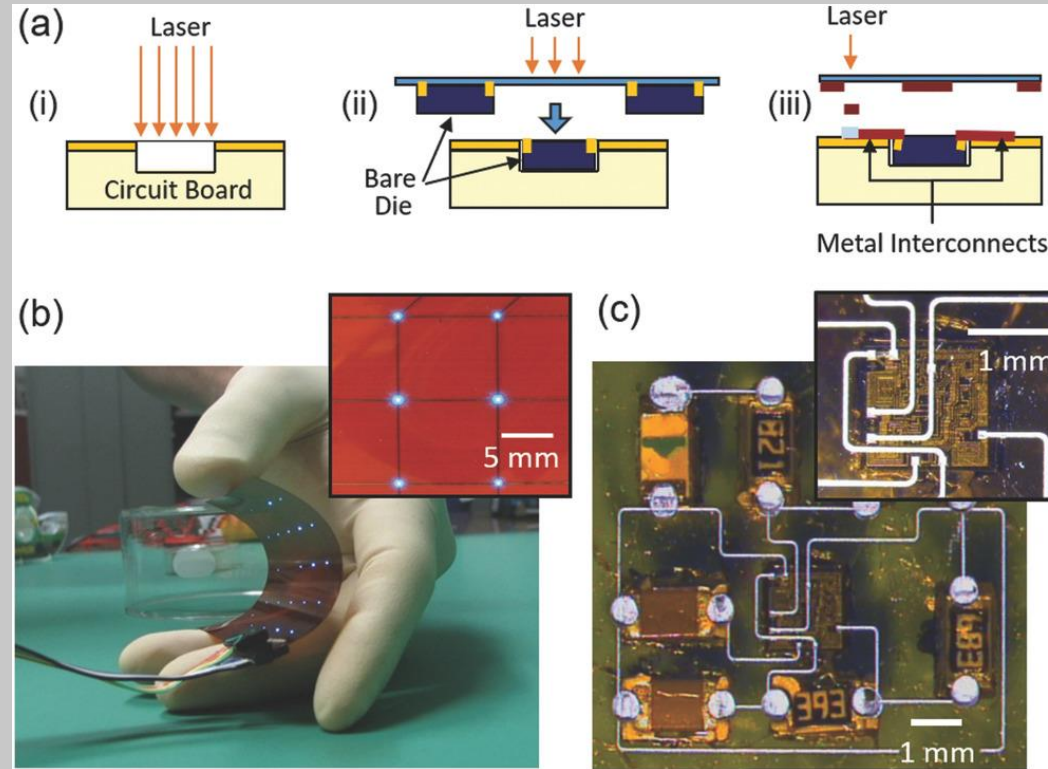


LIFT applications

Printing Silver Nanopastes for interconnection bonding of Au pads

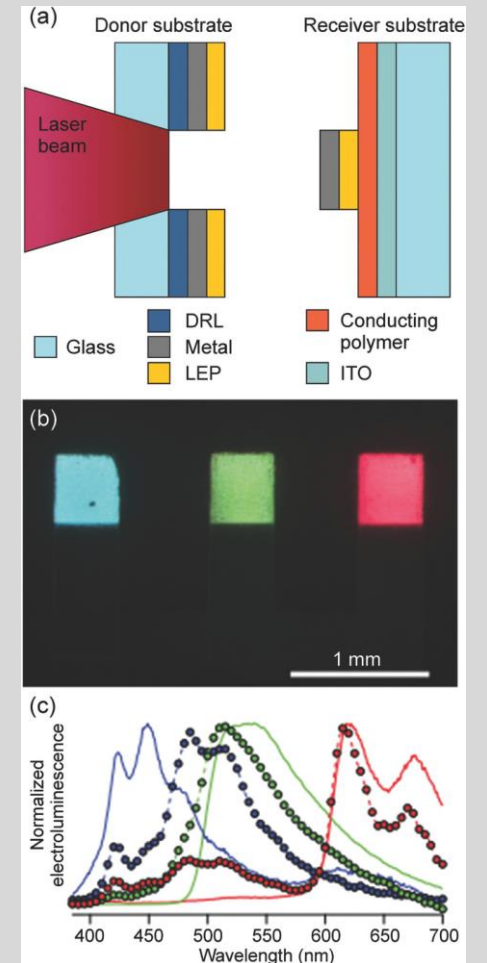


Laser mediated embedded electronics



A. Piqué, R. C. Y. Auyeung, H. Kim, N. A. Charipar, S. A. Mathews, *J. Phys. D: Appl. Phys.* 2016, 49, 223001.

Single-step laser printing of multistack OLEDs through a DRL

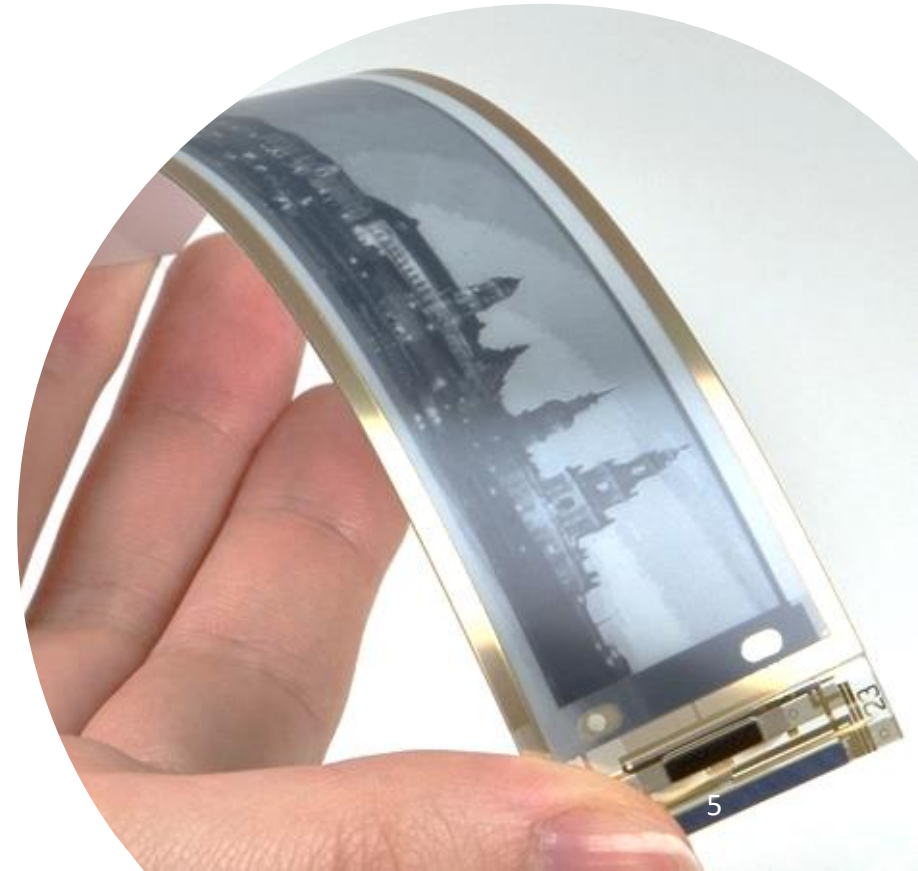
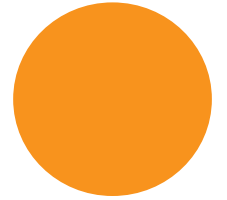


J. Shaw-Stewart, T. Lippert, M. Nagel, F. Nüesch, A. Wokaun, *Appl. Phys. Lett.* 2012, 100, 203303

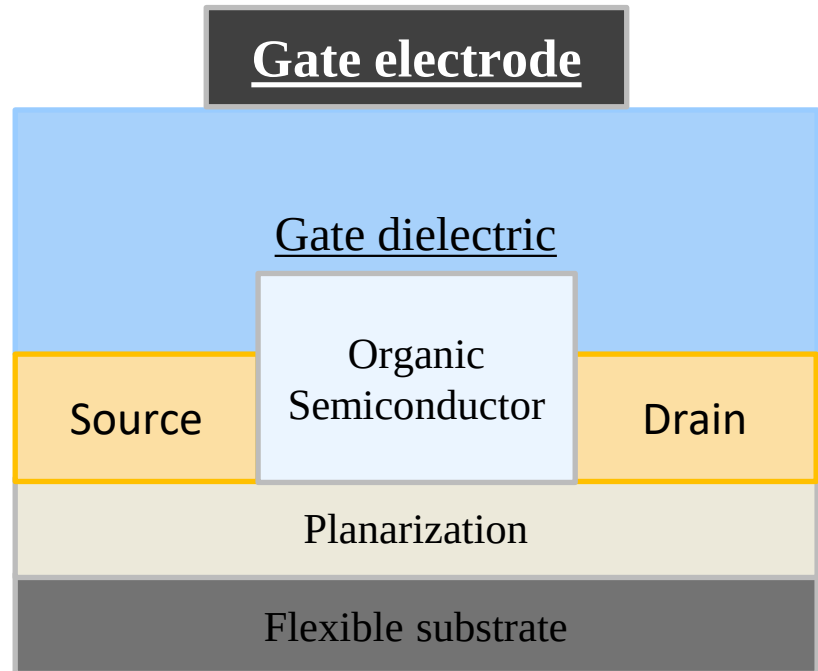


Organic thin film transistor displays

- Lightweight
- Simple fabrication methods
- Inexpensive
- Flexible
- Durability



Organic thin film transistor (OTFT)



OTFT stack schematic representation

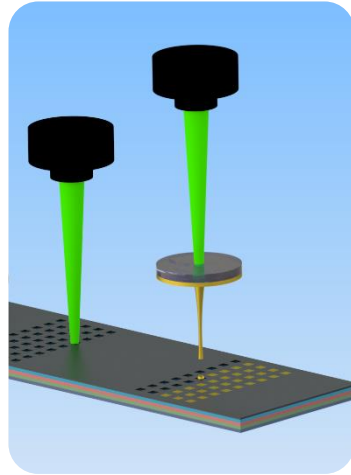
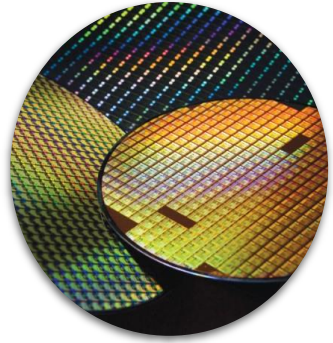
- Photolithography masks to be designed and ordered
- Not fully compatible with complex non-planar patterned substrates due to waviness
- Gate dielectric thermally sensitive ($T_g < 120^\circ\text{C}$)



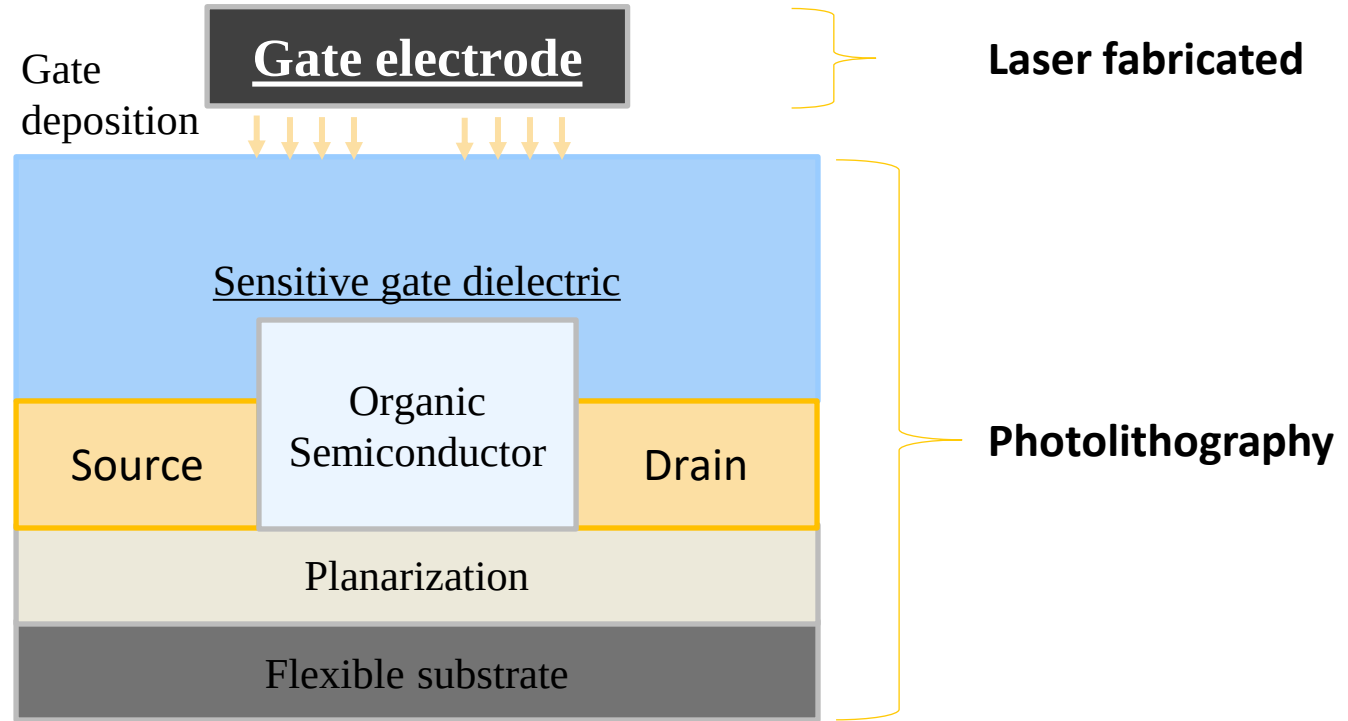
LIFT & photolithography for OTFTs

Photolithography

Laser Printing + Laser sintering



Flexible & Wearable electronics

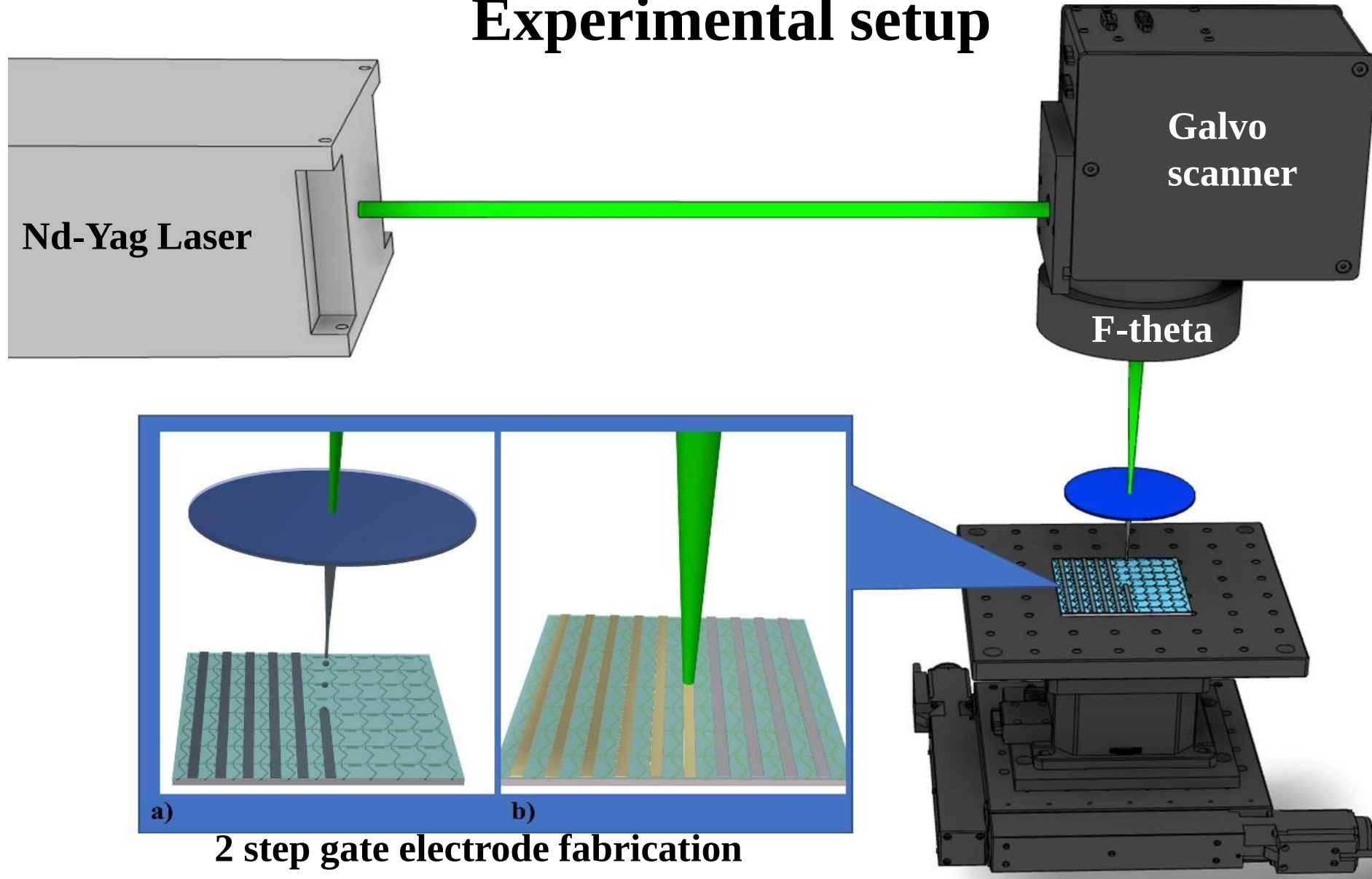


R@LA-FLEX

FlexEnable
Truly flexible electronics

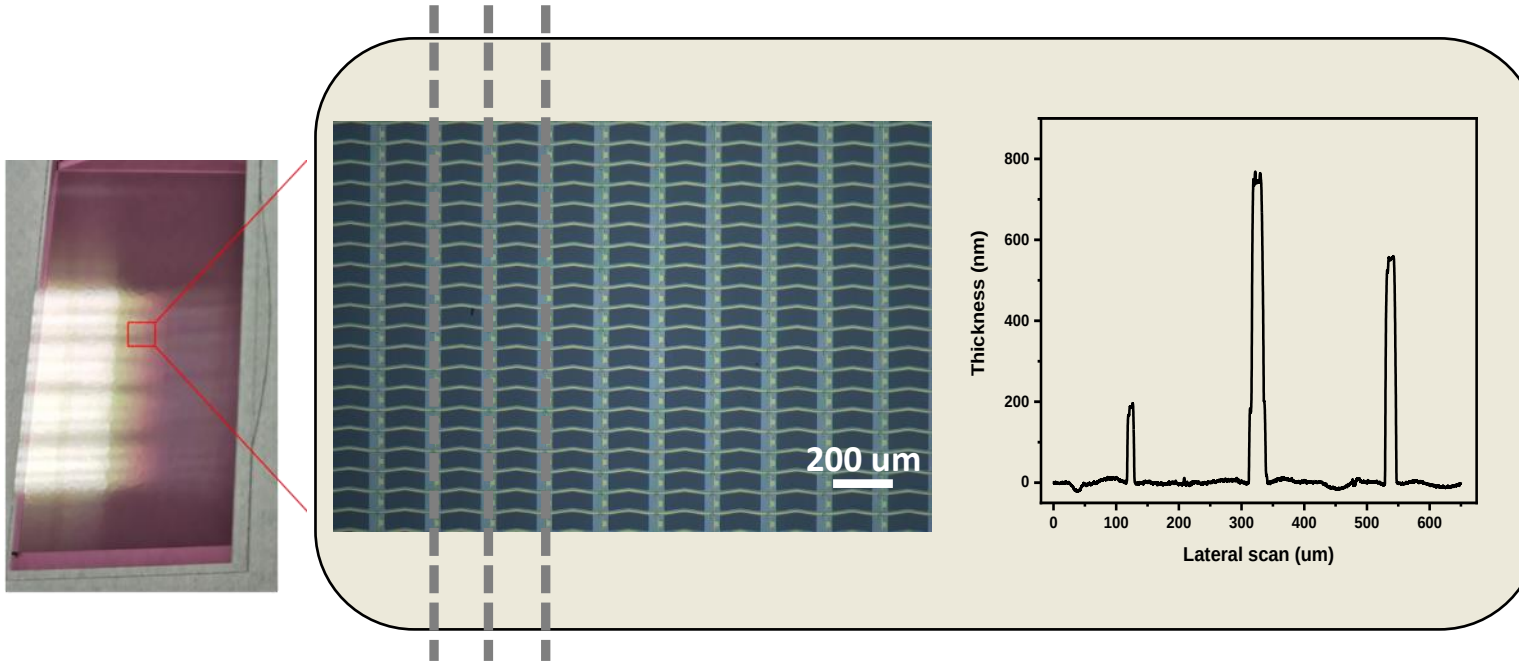


Experimental setup

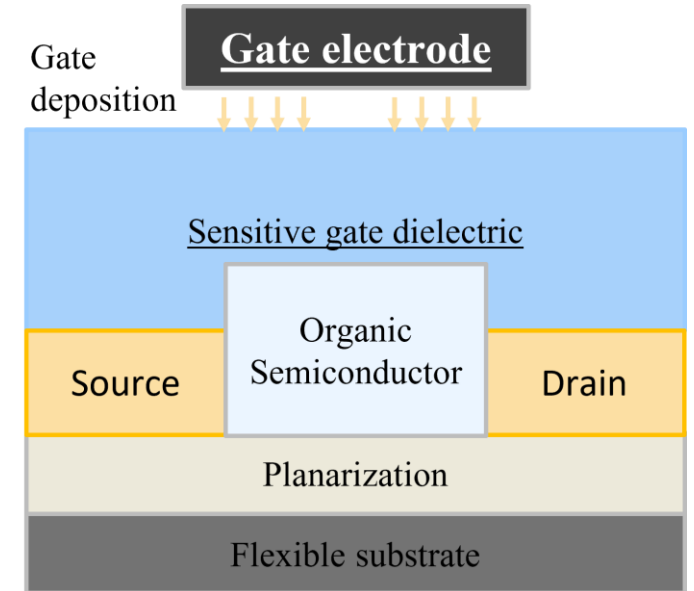


Non-planar substrates

Complex non-planar multilayered OTFT backplane with to be-fabricated gate electrodes (Top view)



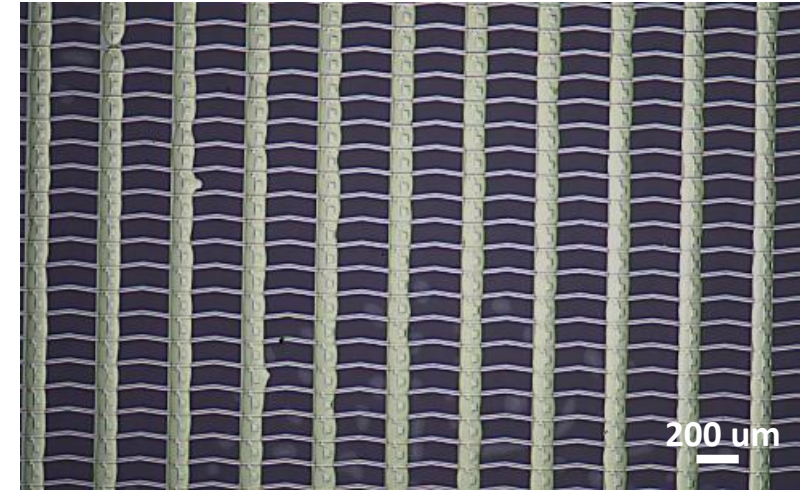
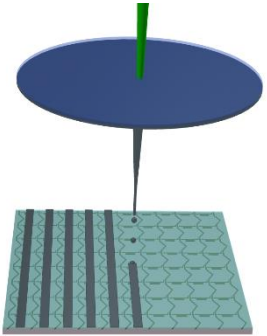
Underlying structures affect the gate dielectric's morphology



Gate electrode printing

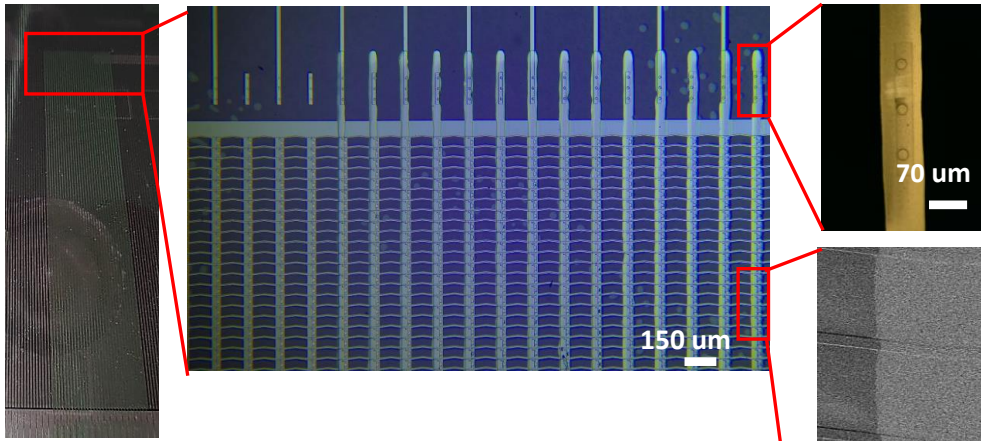
Pitch 100 μm

Laser printing



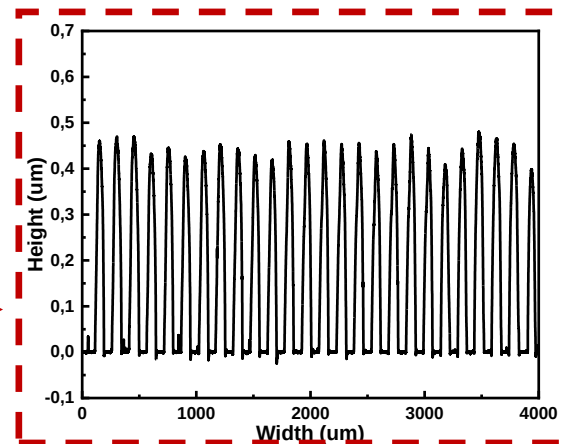
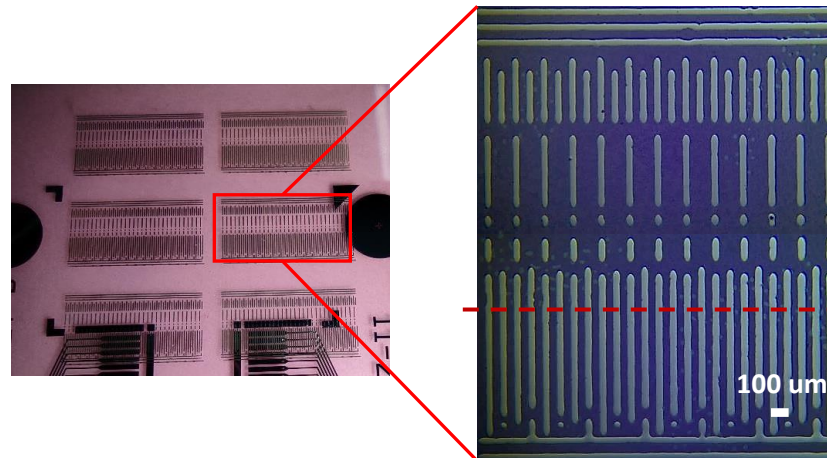
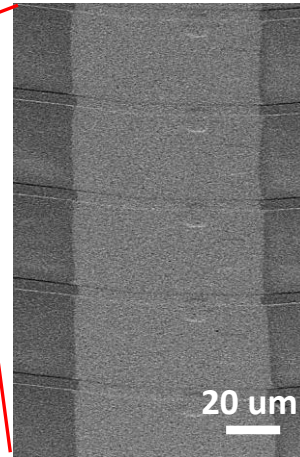
- < 500 nm height
- < 80 μm width
- cm long lines printable on planar and non-planar substrates

Gate electrode printing and sintering



Gate lines for pixel active area

- Laser printed and sintered conductive lines on planar and non-planar substrates exhibiting 400 nm conformity
- Reliable large scale printed integrated gate drivers
- Resistivity values $< 25 \mu\text{Ohm} \cdot \text{cm}$

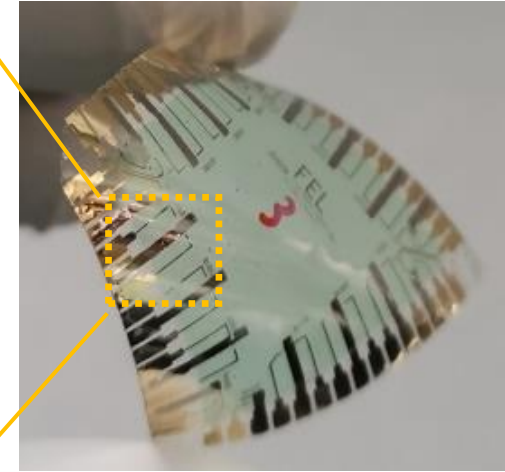
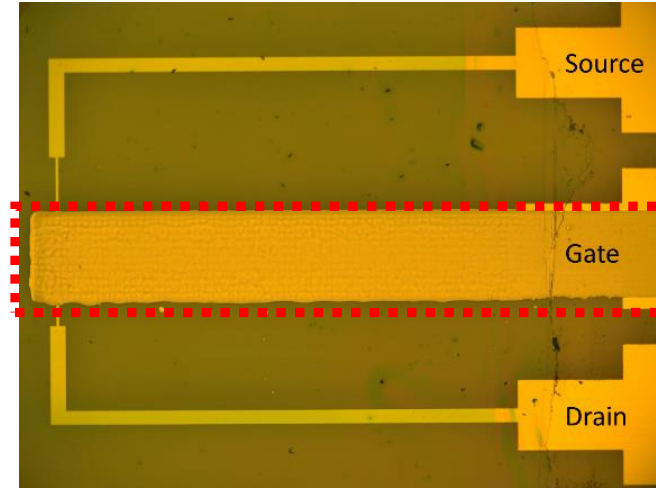


Integrated gate drivers for flexible bezel-less display

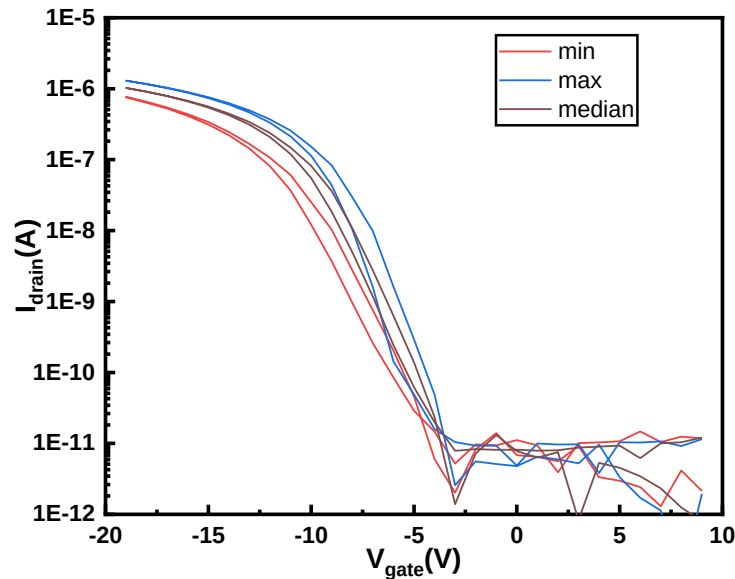
Flexible Organic TFT for Full HD Organic LCD – performance evaluation

Comparison of LIFT with standard manufacturing techniques

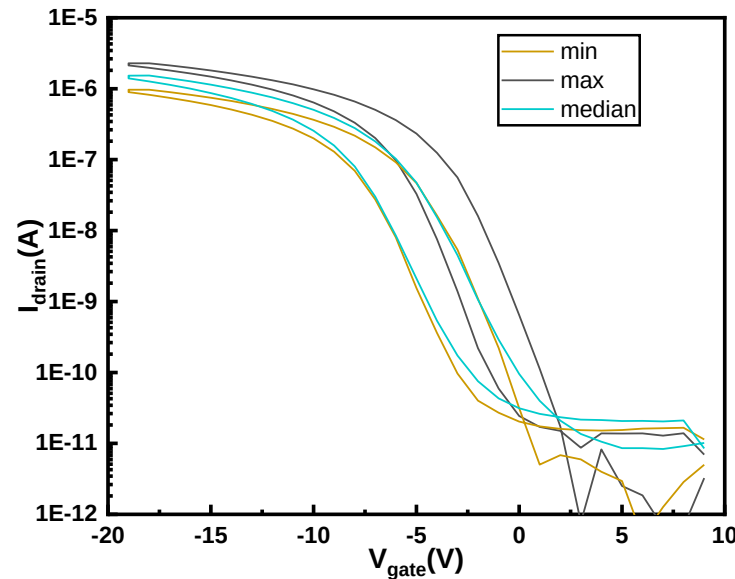
Laser printed and sintered test element



LIFT printed gate



Sputtering deposited gate

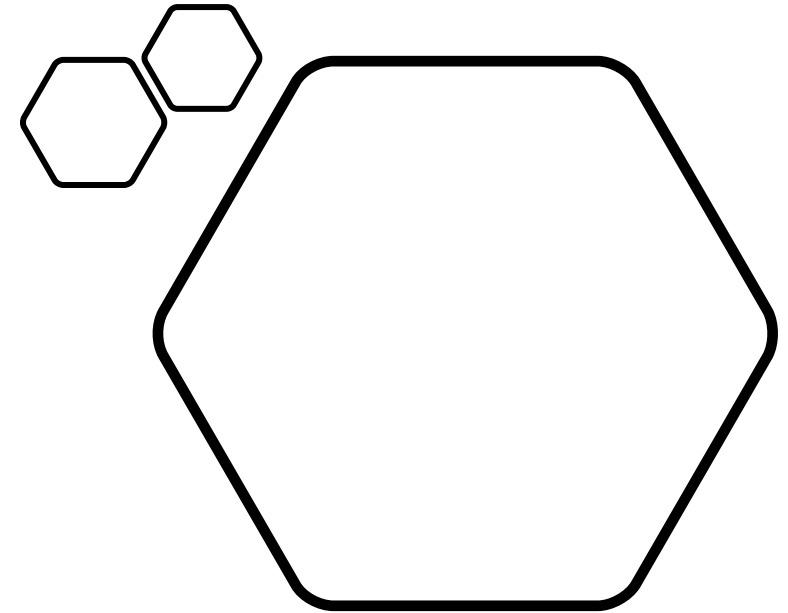


Mobility only decreased by 10% from 1 $\text{cm}^2/(\text{V}\cdot\text{s})$ (sputtering process) to 0.9 $\text{cm}^2/(\text{V}\cdot\text{s})$ (laser processing)

- V_{th} increased by less than 5V
- Ion reduced by less than 50%

In Conclusion...

- High spatial resolution (400 nm height) and high speed printing (5 m/sec), ideal for 3D processing
- Large area printing on flexible substrates (cm length lines of 400 nm height)
- High throughput and enhanced uniformity (height std < 50 nm) of the printed and sintered samples
- Capability for additive manufacturing on demanding substrates with waviness up to 800 nm
- Fabrication of highly efficient functional devices (device overall performance drop by less than 50%)



24/08/2022

Acknowledgments

- *Professor I. Zergioti*
- *Dr. I. Theodorakos*
- *Dr. F. Zacharatos*
- *A. Kabla*
- *S. Melamed*
- *F. de la Vega*
- *Y. Porte*
- *P. Too*

R@LA-FLEX

GA No: 862474

Call: H2020-NMBP-TR-IND-2019

Start: 01/05/2020-30/4/2023

Duration: 36 months

Topic: DT-NMBP-18-2019 (IA)





Thank you

